NSN 5961-00-465-8299 Thyristor Semiconductor Device - Page 1 of 1



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Inclosure Material:
Metal
Overall Length:
Between 0.250 inches and 0.340 inches
Overall Diameter:
Between 0.470 inches and 0.500 inches
Mounting Facility Quantity:
2
Electrode Internally-electrically Connected To Case:
Anode
Mounting Method:
Unthreaded hole
Features Provided:
Hermetically sealed case
Semiconductor Material:
Silicon
Voltage Rating In Volts Per Characteristic:
400.0 repetitive peak reverse voltage, peak total value, gate terminal open-circuited
Current Rating Per Characteristic:
100.00 amperes forward current, total rms watts
Power Rating Per Characteristic:
16.0 watts small-signal input power, common-collector blank
Maximum Operating Tempurature Per Measurement Point:
100.0 degrees celsius ambient air
Test Data Document:
37695-619094 drawing (this is the basic governing drawing, such as a contractor drawing, original equipment manufacturer drawing, etc.
excludes any specification, standard or other document that may be referenced in a basic governing drawing)
Terminal Type And Quantity:
1 case and 2 pin
Shelf Life:
N/a
Unit Of Measure:
Demilitarization:
No
Fiig:
A110a0